



(T_J=25 unless otherwise noted)

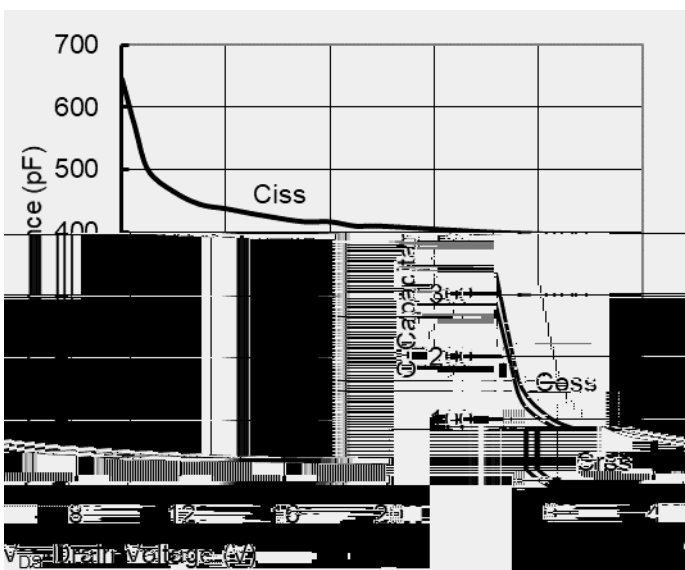
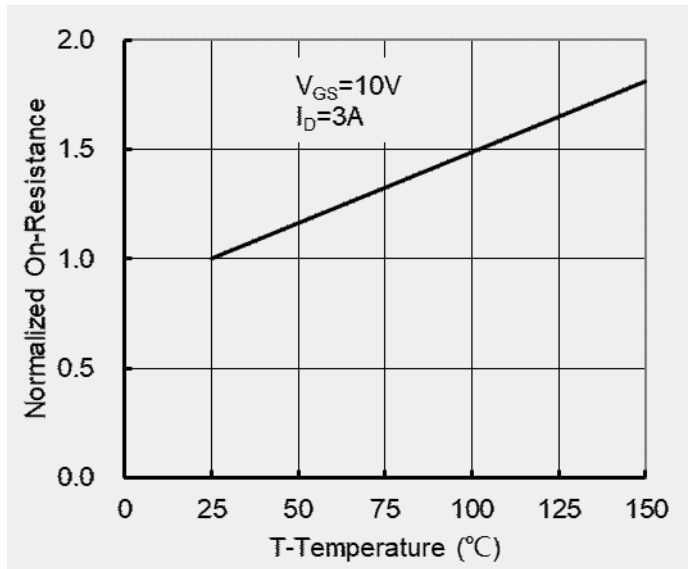
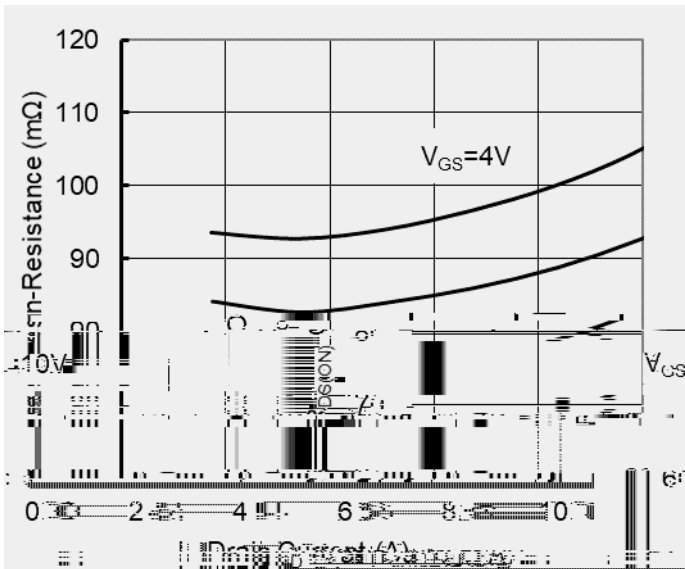
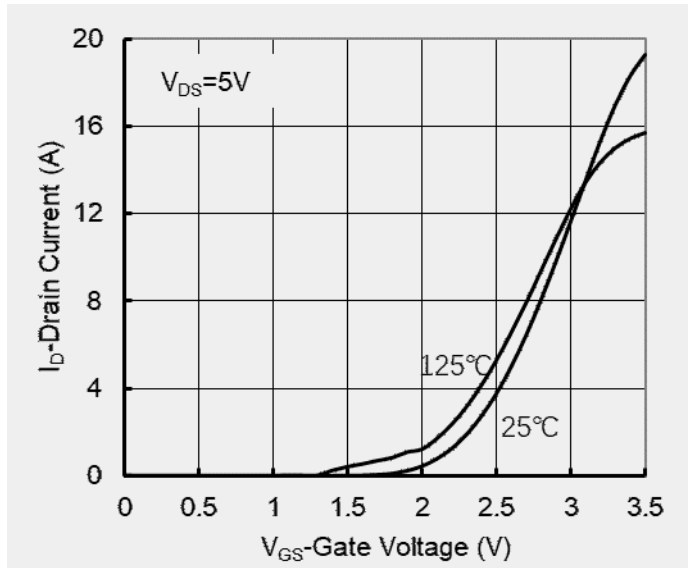
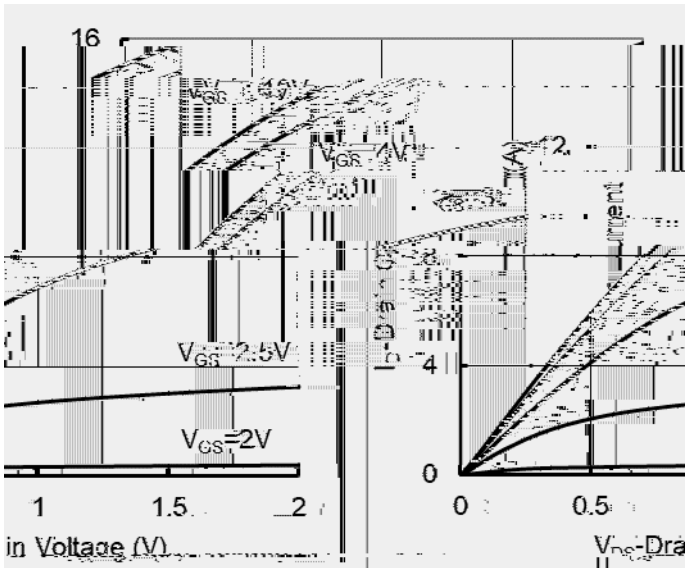
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|-----------------------------------|---------------------|--|-----|-----|------|----|
| | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V, I _D =250μA | 60 | | | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =60V, V _{GS} =0V | | | 1 | μA |
| Gate-Body Leakage Current | I _{GSS1} | V _{GS} =±20V, V _{DS} =0V | | | ±100 | nA |
| | I _{GSS2} | V _{GS} =±10V, V _{DS} =0V | | | ±50 | |
| Gate Threshold Voltage | V _{GS(th)} | V _{DS} =V _{GS} , I _D =250μA | 0.9 | 1.3 | 2.0 | V |
| Static Drain-Source On-Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =3A | | 86 | 100 | m |
| | | V _{GS} =4.5V, I _D =2A | | 92 | 120 | |
| Diode Forward Voltage | V _{SD} | I _S =3A, V _{GS} =0V | | | 1.2 | V |
| | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} =10V, V _{GS} =0V, f=1MHZ | | 409 | | pF |
| Output Capacitance | C _{oss} | | | 50 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 41 | | |

Total Gate Charge

Q_g

V_{GS}=10V, V_{DS}=30V, I_D=3A

Å



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'LVFODLPHU

7KH LQIRUPDWLRQ SGRV ~~FRMCH~~ ' ~~FDG~~ ° ~~M~~ ~~KLD~~ ~~QSA~~